TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

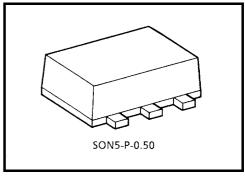
TC7SH126FE

Bus Buffer

Features

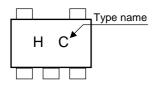
High speed: t_{pd} = 3.8 ns (typ.) at V $_{\rm CC}$ = 5 V Low power dissipation: $I_{\rm CC}$ = 2 μA (max) at Ta = 25°C High noise immunity: V $_{\rm NIH}$ = V $_{\rm NIL}$ = 28% V $_{\rm CC}$ (min) 5.5V tolerant input.

Wide operating voltage range: $V_{\rm CC}$ (opr) = 2~5.5 V

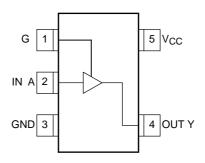


Weight: 0.003 g (typ.)

Marking



Pin Assignment (top view)



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7	V
DC input voltage	V _{IN}	-0.5~7	V
DC output voltage	Vout	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	Гок	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	150	mW
Storage temperature	T _{stg}	-65~150	°C

Logic Diagram



Truth Table

G	Α	Υ
L	Х	Z
Н	L	L
Н	Н	Н

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	2~5.5	V	
Input voltage	V _{IN}	0~5.5	V	
Output voltage	V _{OUT}	0~ V _{CC}	V	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 V \pm 0.3 V)	ns/V	
input rise and rail tille	ui/uv	0~20 (V_{CC} = 5 V ± 0.5 V)		

Electrical Characteristics

DC Characteristics

Characteristics Symbol		Test	Lest Condition -			Ta = 25°C			Ta = -40~85°C		Unit
		Circuit			V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
High-level input			_		2.0	1.5	_	_	1.5	_	V
voltage VIH -	_	3.0~5.5			V _{CC} × 0.7		_	V _{CC} × 0.7			
Low-level input					2.0	_	_	0.5	_	0.5	
voltage	_		_	3.0~5.5	_	_	V _{CC} × 0.3	_	V _{CC} × 0.3	V	
					2.0	1.9	2.0	_	1.9	_	
		он —	V _{IN} = V _{IH}	I _{OH} = -50 μA	3.0	2.9	3.0	_	2.9	_	V
High-level output voltage	High-level VOH				4.5	4.4	4.5	_	4.4	_	
				I _{OH} = -4 mA	3.0	2.58	_	_	2.48	_	
				$I_{OH} = -8 \text{ mA}$	4.5	3.94		_	3.80		
					2.0	_	0	0.1	_	0.1	
			I _{OL} = 50 μA	3.0	_	0	0.1		0.1		
Low-level output voltage	Low-level output VOL	V _{OL} —	V _{IN} = V _{IH} or V _{IL}		4.5	_	0	0.1		0.1	V
				I _{OL} = 4 mA	3.0	_	_	0.36		0.44	
				I _{OL} = 8 mA	4.5	_	_	0.36		0.44	
Input leakage current	I _{IN}	_	V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent supply current	Icc	_	V _{IN} = V _{CC} or GND		5.5	_		2.0	_	20.0	μΑ

AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Circuit	Test Condition		n		Ta = 25°C		Ta = -40~85°C		Unit
Onaracteristics Syll	Symbol			V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
				3.3 ± 0.3	15	_	5.6	8.0	1.0	9.5	
Propagation delay	t _{pLH}			3.5 ± 0.5	50	_	8.1	11.5	1.0	13.0	ns
time	t_{pHL}		_	5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5	115
				5.0 ± 0.5	50	_	5.3	7.5	1.0	8.5	
	t _{pZL}			3.3 ± 0.3	15	_	5.4	8.0	1.0	9.5	
3-state output enable time					50	_	7.9	11.5	1.0	13.0	
	t _{pZH}		5.0 ± 0.5	15	_	3.6	5.1	1.0	6.0	ns	
				5.0 ± 0.5	50	_	5.1	7.1	1.0	8.0	
3-state output	t _{pLZ}			3.3 ± 0.3	50	_	9.5	13.2	1.0	15.0	ns
disable time	t _{pHZ}		_	5.0 ± 0.5	50	_	6.1	8.8	1.0	10.0	115
Input capacitance	C _{IN}	_		_		_	4	10	_	10	pF
Output capacitance	C _{OUT}	_		_		_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}				(Note)	_	14	_		_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

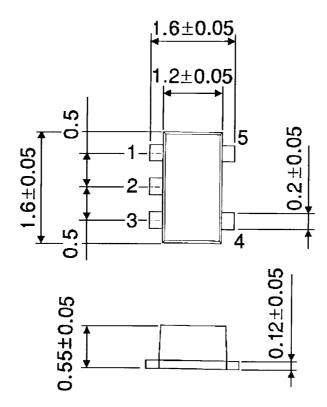
Average operating current can be obtained by the equation.

$$I_{CC\;(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$



Package Dimensions

SON5-P-0.50 Unit: mm



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Weight: 0.003 g (typ.)

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TC7SH126FE

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